



STP11NM80 - STB11NM80 STF11NM80 - STW11NM80

N-CHANNEL 800V - 0.35Ω - 11A TO-220/FP/D²PAK/TO-247

MDmesh™ Power MOSFET

TARGET DATA

TYPE	V _{DSS}	R _{DS(on)}	R _{ds(on)} *Q _g	I _D
STP11NM80	800 V	< 0.40 Ω	14 Ω*nC	11 A
STF11NM80	800 V	< 0.40 Ω	14 Ω*nC	11 A
STB11NM80	800 V	< 0.40 Ω	14 Ω*nC	11 A
STW11NM80	800 V	< 0.40 Ω	14 Ω*nC	11 A

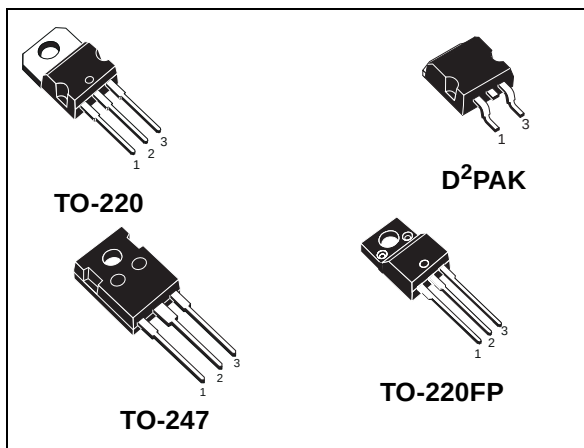
- TYPICAL R_{DS(on)} = 0.35 Ω
- LOW GATE INPUT RESISTANCE
- LOW INPUT CAPACITANCE AND GATE CHARGE
- BEST R_{ds(on)} * Q_g IN THE INDUSTRY

DESCRIPTION

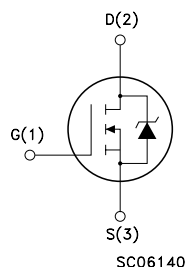
The MDmesh™ is a new revolutionary MOSFET technology that associates the Multiple Drain process with the Company's PowerMESH™ horizontal layout. The resulting product has an outstanding low on-resistance, impressively high dv/dt and excellent avalanche characteristics. The adoption of the Company's proprietary strip technique yields overall dynamic performance that is significantly better than that of similar competition's products.

APPLICATIONS

The 800 V MDmesh™ family is very suitable for single switch applications in particular for Flyback and Forward converter topologies.



INTERNAL SCHEMATIC DIAGRAM



ORDERING INFORMATION

SALES TYPE	MARKING	PACKAGE	PACKAGING
STP11NM80	P11NM80	TO-220	TUBE
STF11NM80	F11NM80	TO-220FP	TUBE
STB11NM80T4	B11NM80	D ² PAK	TAPE & REEL
STW11NM80	W11NM80	TO-247	TUBE

STP11NM80 - STB11NM80 - STF11NM80 - STW11NM80

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		TO-220/D ² PAK TO-247	TO-220FP	
V _{DS}	Drain-source Voltage (V _{GS} = 0)	800		V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	800		V
V _{GS}	Gate- source Voltage	± 30		V
I _D	Drain Current (continuous) at T _C = 25°C	11	11 (*)	A
I _D	Drain Current (continuous) at T _C = 100°C	4.7	4.7 (*)	A
I _{DM} (•)	Drain Current (pulsed)	44	44 (*)	A
P _{TOT}	Total Dissipation at T _C = 25°C	150	35	W
	Derating Factor	1.2	0.28	W/°C
dv/dt(1)	Peak Diode Recovery voltage slope	15		V/ns
T _{stg}	Storage Temperature	-65 to 150		°C
T _j	Max. Operating Junction Temperature			

(•) Pulse width limited by safe operating area

(1) I_{SD} < 11A, di/dt < 400A/μs, V_{DD} < V_{(BR)DSS}, T_J < T_{JMAX}

(*) Limited only by the Maximum Temperature Allowed

THERMAL DATA

		TO-220/D ² PAK TO-247	TO-220FP	
R _{thj-case}	Thermal Resistance Junction-case Max	0.83	3.6	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient Max	62.5		°C/W
T _l	Maximum Lead Temperature For Soldering Purpose	300		°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max)	TBD	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = 2.5A, V _{DD} = 50 V)	TBD	mJ

ELECTRICAL CHARACTERISTICS (T_{CASE} = 25 °C UNLESS OTHERWISE SPECIFIED) ON/OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0	800			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C			10 100	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ±30V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	3	4	5	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10 V, I _D = 5.5 A		0.35	0.40	Ω

ELECTRICAL CHARACTERISTICS (CONTINUED)

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$, $I_D = 7.5$ A		5		S
C_{iss}	Input Capacitance	$V_{DS} = 30$ V, $f = 1$ MHz, $V_{GS} = 0$		1900		pF
C_{oss}	Output Capacitance			1000		pF
C_{rss}	Reverse Transfer Capacitance			18		pF
R_G	Gate Input Resistance	$f=1$ MHz Gate DC Bias = 0 Test Signal Level = 20mV Open Drain		2		Ω

(1) Pulsed: Pulse duration = 300 μ s, duty cycle 1.5 %.

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 400$ V, $I_D = 5.5$ A $R_G = 4.7$ Ω , $V_{GS} = 10$ V (see test circuit, Figure 3)		27		ns
t_r	Rise Time			14		ns
Q_g	Total Gate Charge	$V_{DD} = 400$ V, $I_D = 11$ A, $V_{GS} = 10$ V		40	58	nC
Q_{gs}	Gate-Source Charge			10		nC
Q_{gd}	Gate-Drain Charge			24		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 640$ V, $I_D = 11$ A, $R_G = 4.7$ Ω , $V_{GS} = 10$ V (see test circuit, Figure 5)		6		ns
t_f	Fall Time			11		ns
t_c	Cross-over Time			21		ns

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				11	A
I_{SDM} (2)	Source-drain Current (pulsed)				44	A
V_{SD} (1)	Forward On Voltage	$I_{SD} = 11$ A, $V_{GS} = 0$			1.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 11$ A, $di/dt = 100$ A/ μ s, $V_{DD} = 100$ V, $T_j = 150^\circ$ C (see test circuit, Figure 5)		496		ns
Q_{rr}	Reverse Recovery Charge			6.5		μ C
I_{RRM}	Reverse Recovery Current			26		A

Note: 1. Pulsed: Pulse duration = 300 μ s, duty cycle 1.5 %.

2. Pulse width limited by safe operating area.

Fig. 1: Unclamped Inductive Load Test Circuit

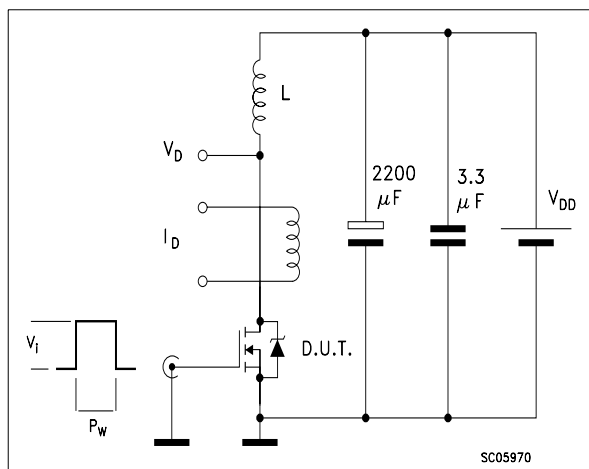


Fig. 2: Unclamped Inductive Waveform

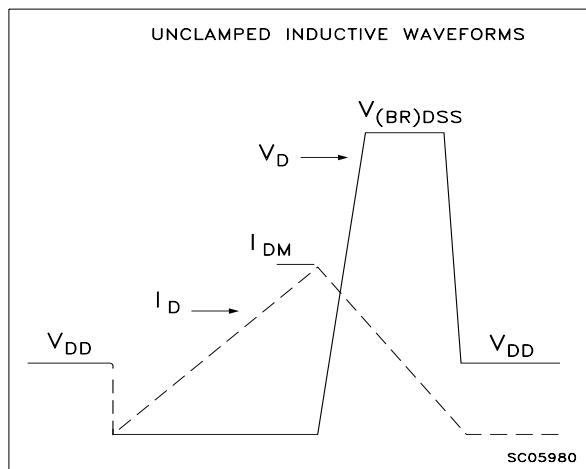


Fig. 3: Switching Times Test Circuit For Resistive Load

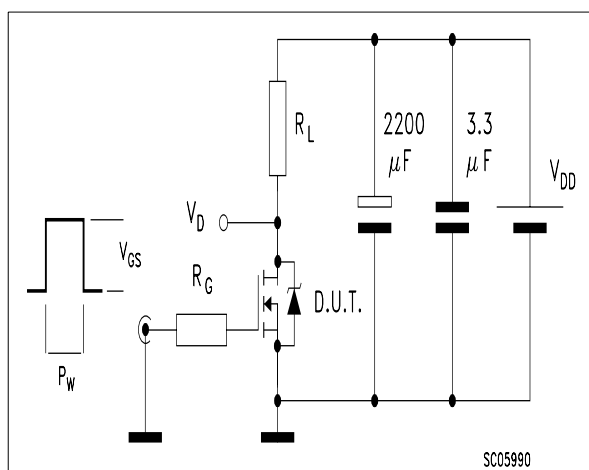


Fig. 4: Gate Charge test Circuit

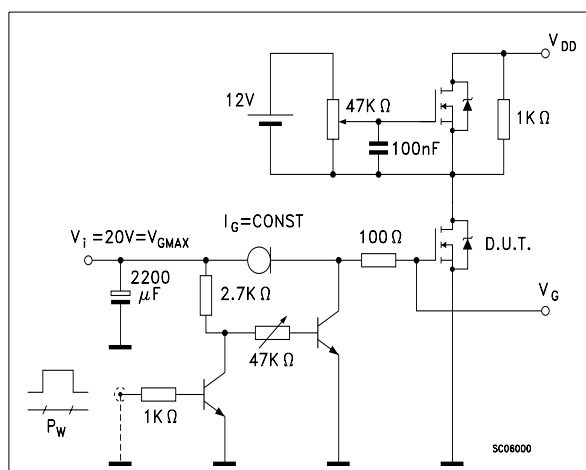
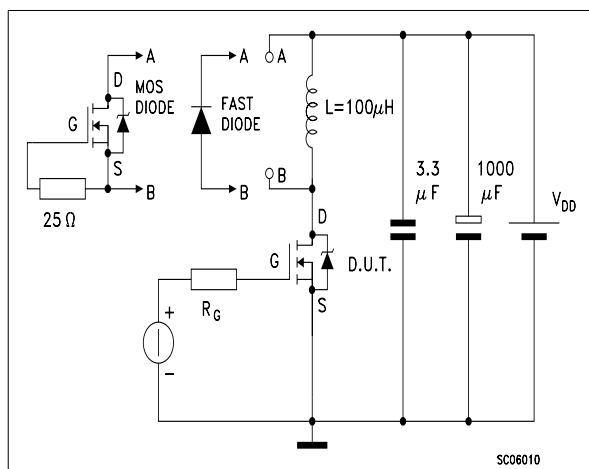
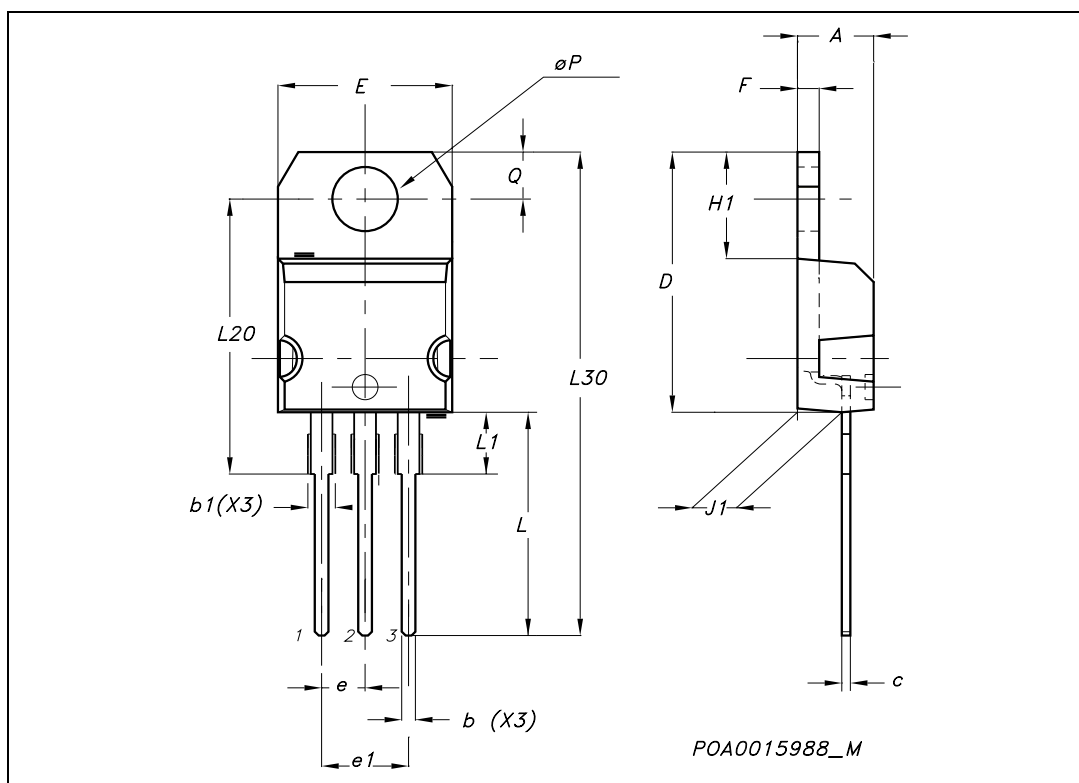


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



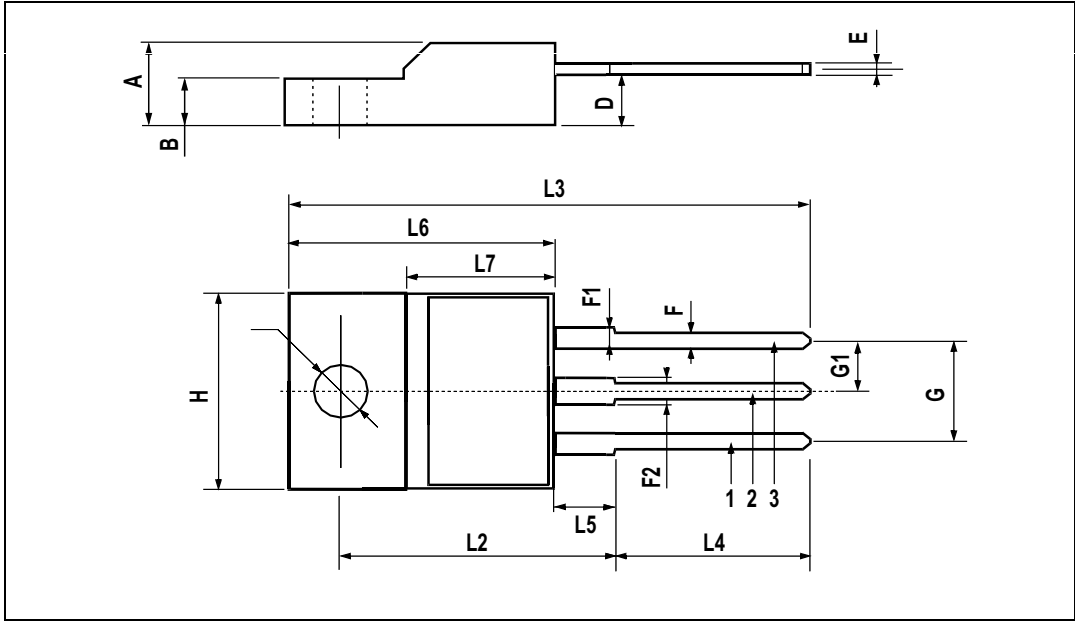
TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



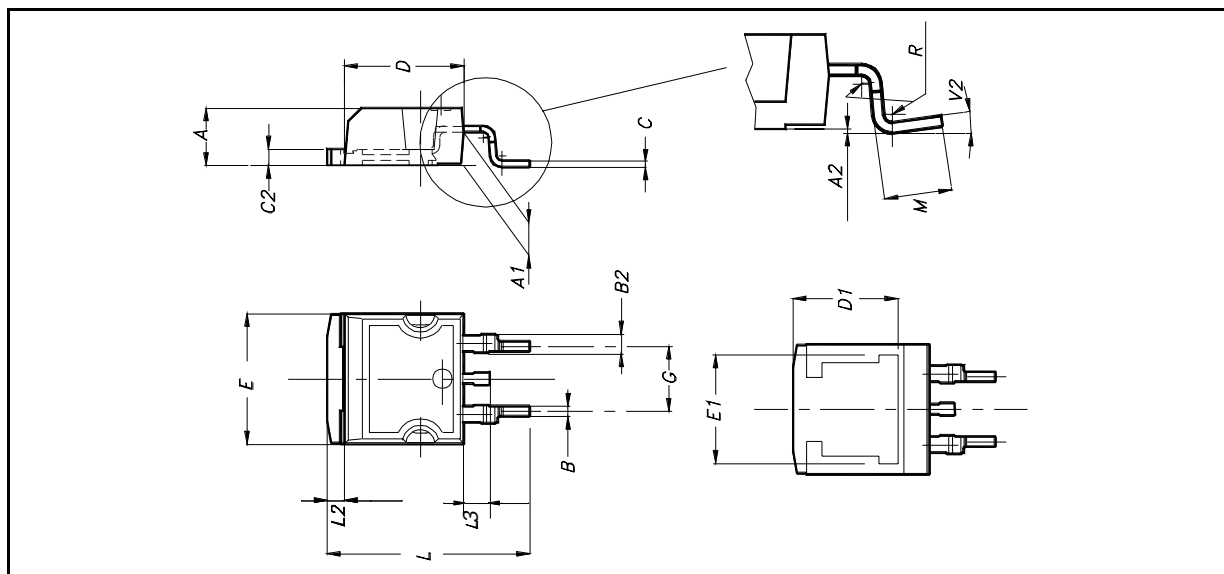
TO-220FP MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



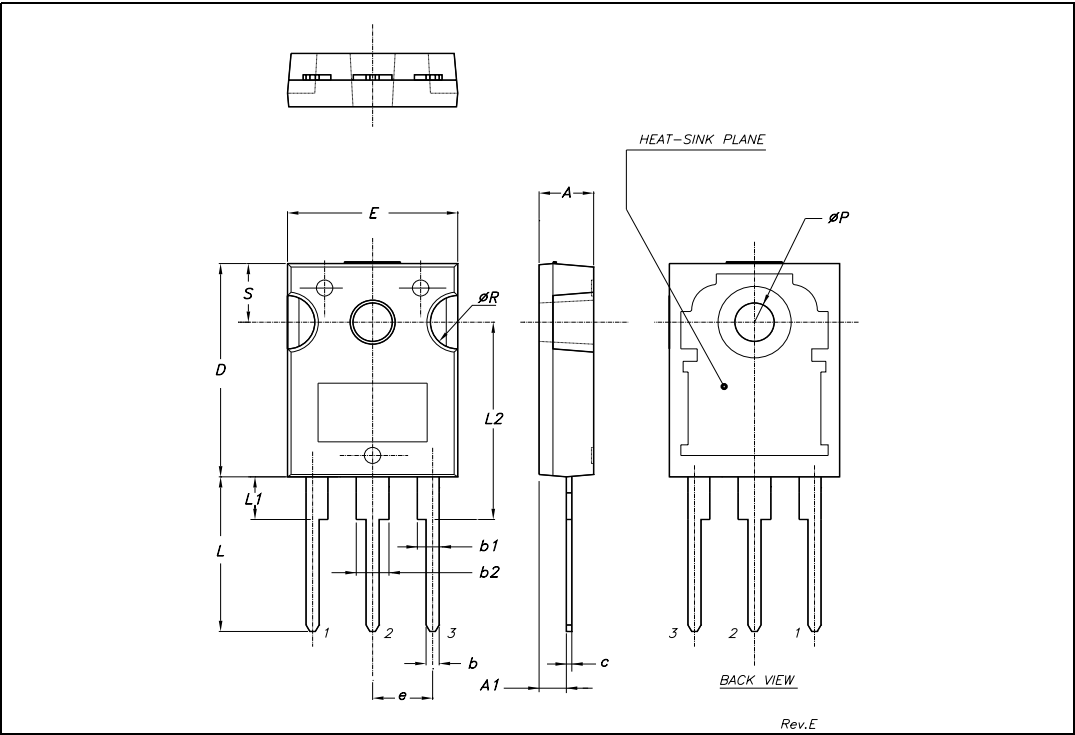
D²PAK MECHANICAL DATA

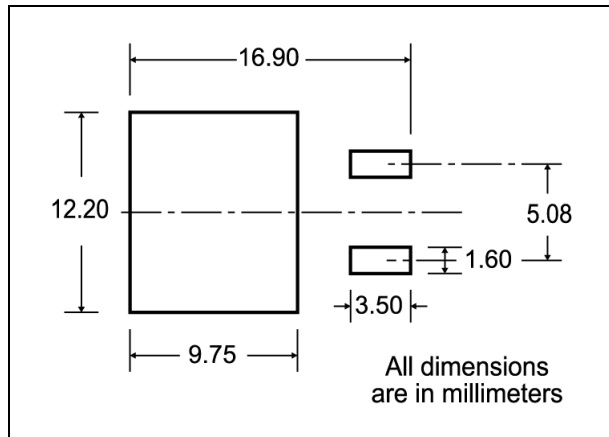
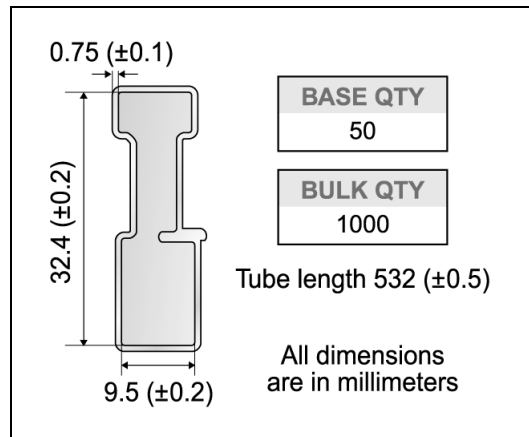
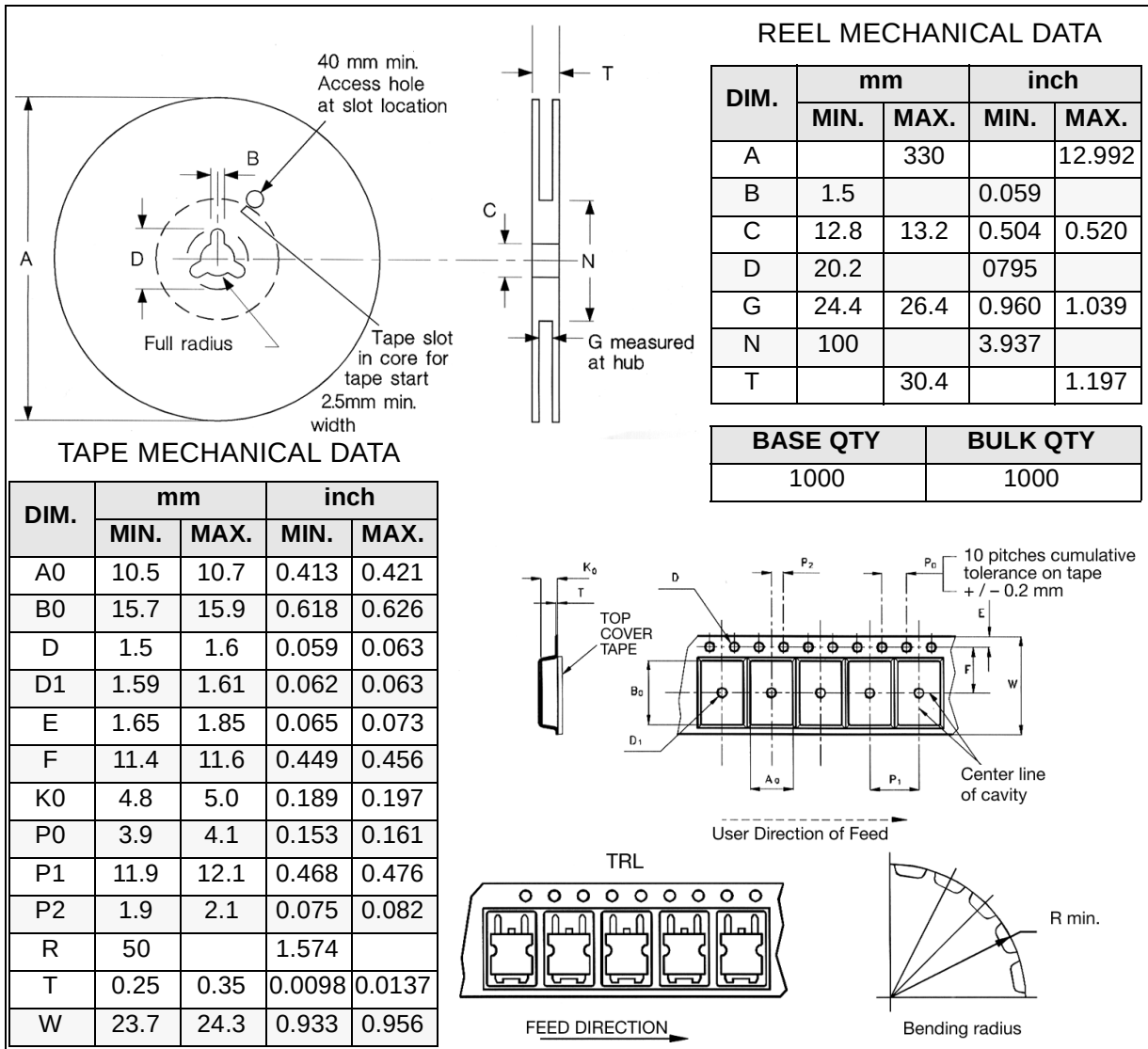
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		8°			



TO-247 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.85		5.15	0.19		0.20
A1	2.20		2.60	0.086		0.102
b	1.0		1.40	0.039		0.055
b1	2.0		2.40	0.079		0.094
b2	3.0		3.40	0.118		0.134
c	0.40		0.80	0.015		0.03
D	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
e		5.45			0.214	
L	14.20		14.80	0.560		0.582
L1	3.70		4.30	0.14		0.17
L2		18.50			0.728	
øP	3.55		3.65	0.140		0.143
øR	4.50		5.50	0.177		0.216
S		5.50			0.216	



D²PAK FOOTPRINT**TUBE SHIPMENT (no suffix)*****TAPE AND REEL SHIPMENT (suffix "T4")***

* on sales type

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